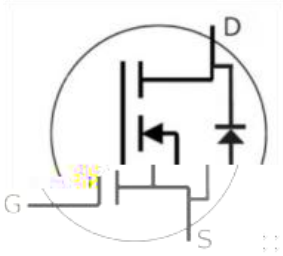
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TriQSiC™ 1700V Silicon Carbide Power MOSFET G2

Features

-
-
-
-
-



Benefits

-
-
-
-
-

Part number	Die size W x L mm

Applications

-
-
-
-

Table 1 Key performance and package parameters

Type	V_{DS}	I_{DS} ≤	$R_{DS(on),\ typ}$	$T_{J,max}$

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1 Maximum ratings

Table 2 Maximum rating

Symbol	Parameter	Value	Unit	Test Conditions	Note

2 Electrical characteristics

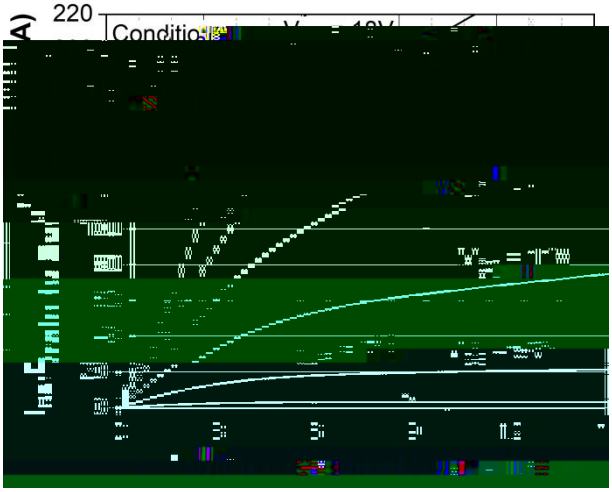
2.1 Static characteristics

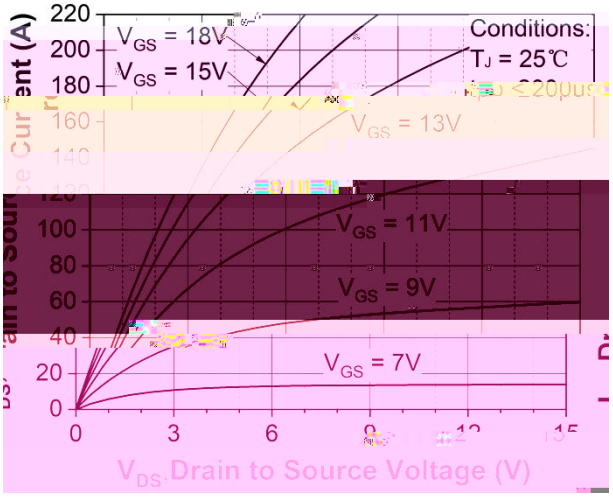
Table 3 Static characteristics

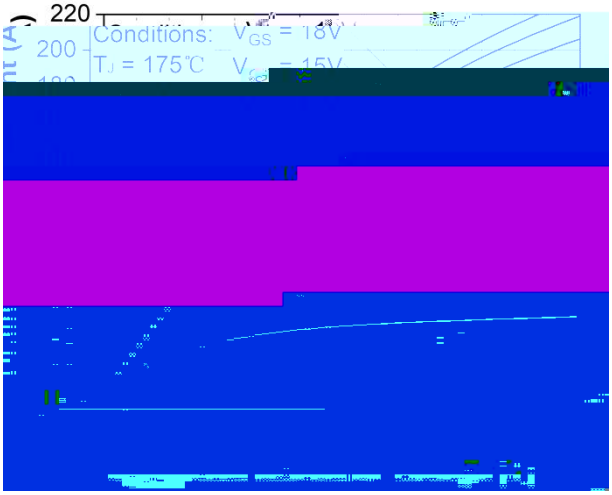
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

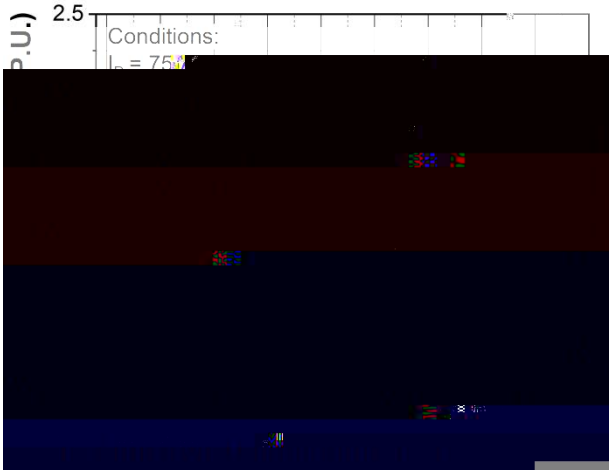
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3 Electrical characteristic diagrams

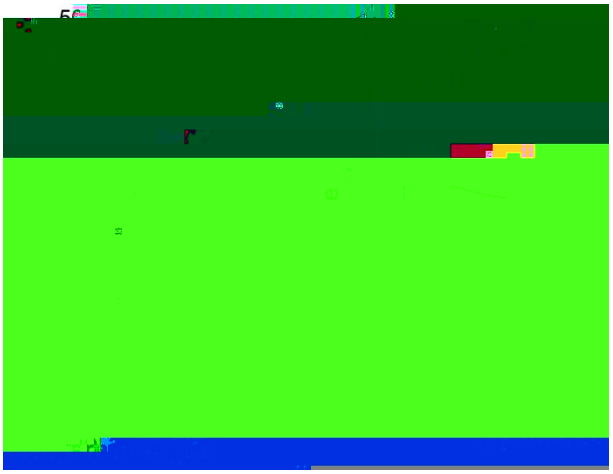




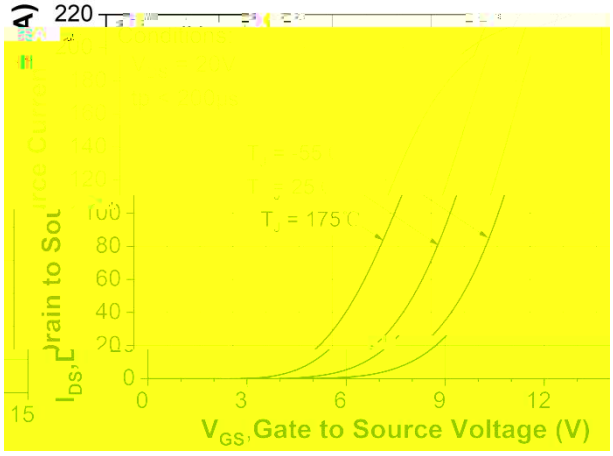


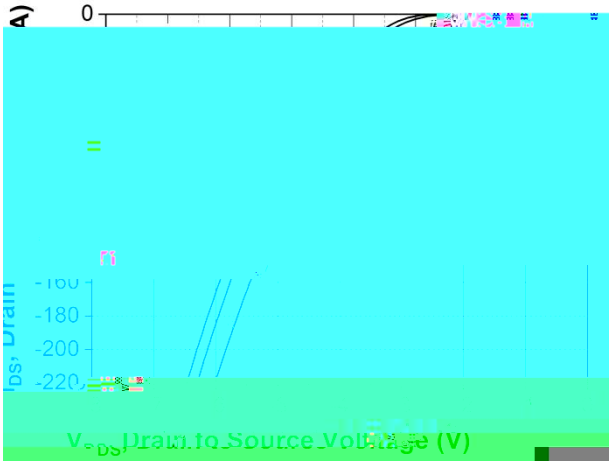


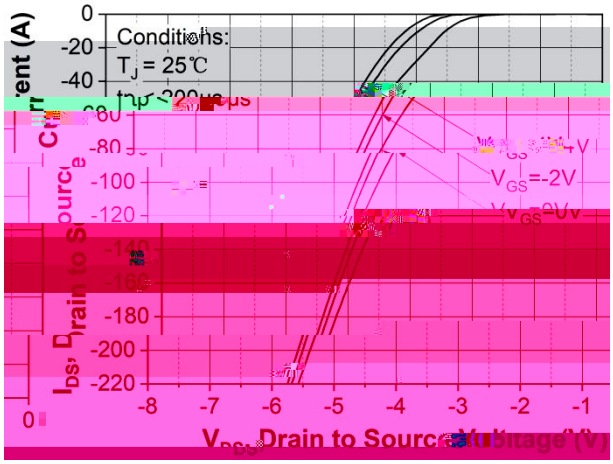


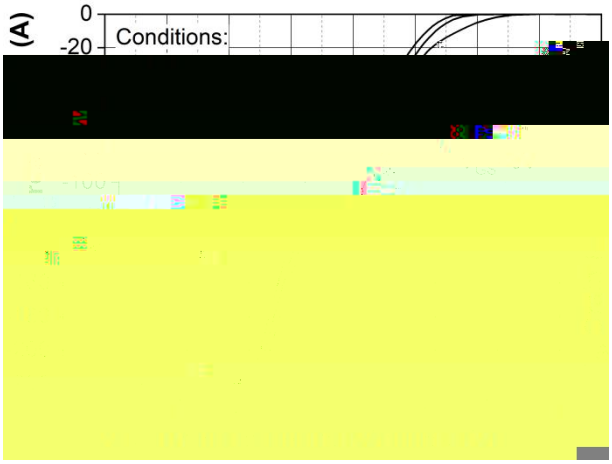


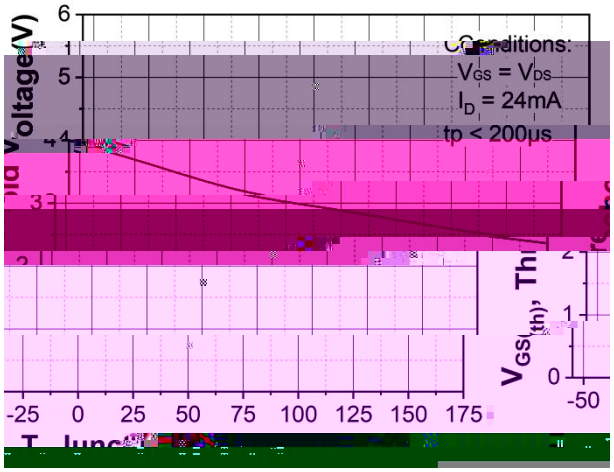
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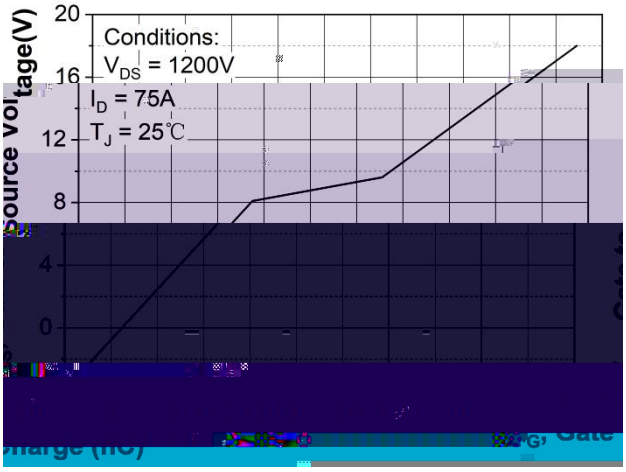












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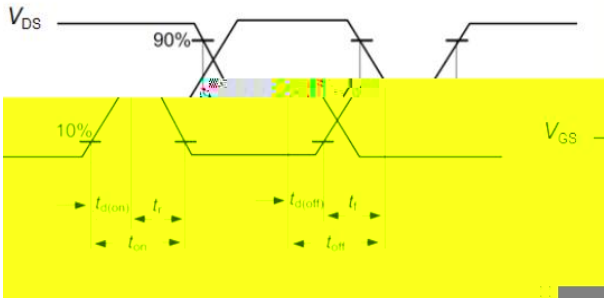
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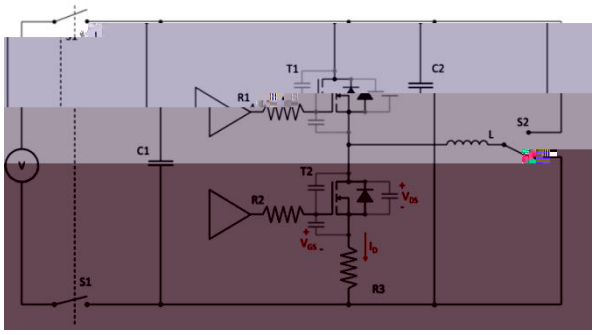
4 Mechanical parameters

4.1 Dimensions and metallization

Parameter	Typical value	Unit	Metallization

5 Test conditions





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1700V SiC Power MOSFET

Revision history

Document version	Date of release	Document stage	Description of changes
V01_00	2024-03-01	——	——
V02_00	2024-09-06	——	——
V02_01	2024-10-25	——	——
V02_02	2025-04-30	——	——
V02_03	2025-09-08	——	——
V02_04	2025-12-30	Final	——

Attention

Rohs compliance

REACH compliance

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